

POWER MANAGEMENT

PRELIMINARY

Description

The SC1302A/B/C family are low cost dual low-side MOSFET drivers. These drivers accept TTL-compatible inputs and are capable of supplying high current outputs (> 2A peak) to external MOSFET's. Fast switching allows operation up to 1 MHz. The SC1302A/B/C is available in three configurations: dual non-inverting, dual inverting and one inverting plus one non-inverting output.

An under-voltage-lock-out circuit guarantees that the driver outputs are low when Vcc is less than 4.5V (typ). An internal temperature sensor shuts down the driver in the event of over temperature. The 8-pin MSOP or SOIC package uses minimum space.

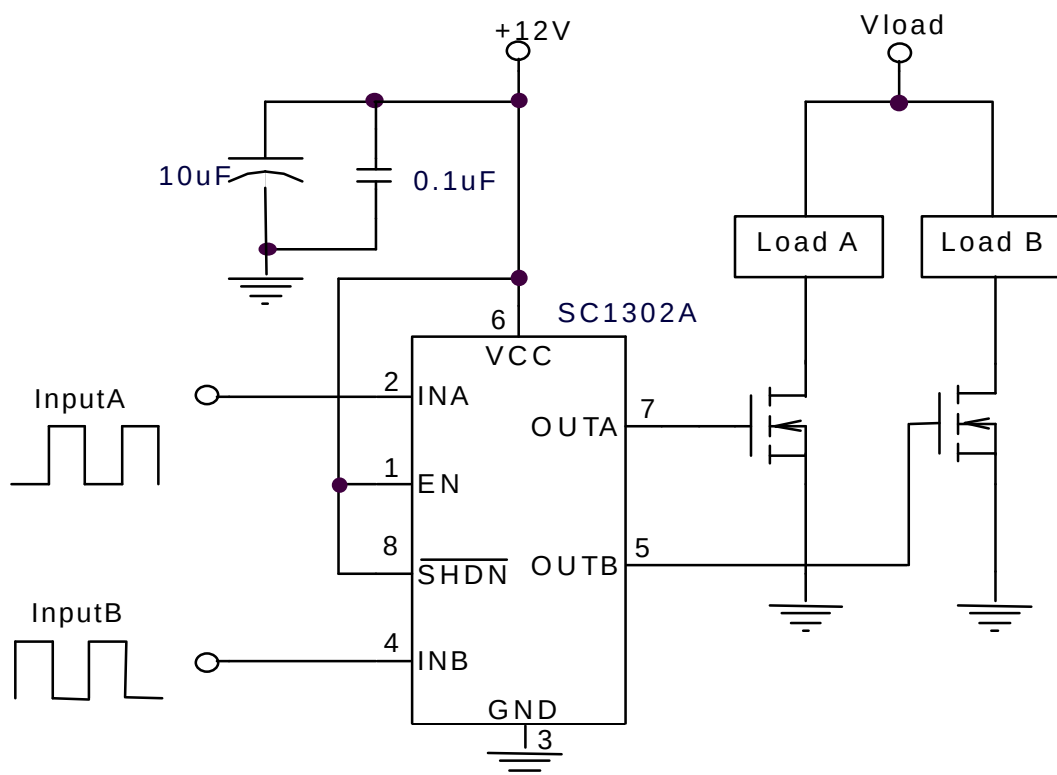
Features

- ◆ +4.5V to +16.5V operation
- ◆ Fast rise and fall times (20ns typical with 1000pf load)
- ◆ Dual MOSFET driver
- ◆ 2A peak drive current
- ◆ 40ns propagation delay
- ◆ 8-pin MSOP/SOIC packages
- ◆ Enable/disable control
- ◆ TTL-compatible input
- ◆ Under voltage lockout with hysteresis
- ◆ Low shutdown supply current
- ◆ Over temperature protection
- ◆ ESD protection
- ◆ Dual inverting/non-inverting and inverting/non-inverting configurations

Applications

- ◆ Switch-mode power supplies
- ◆ Battery powered applications
- ◆ Solenoid and motor drives

Typical Application Circuit



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Absolute Maximum Ratings

Parameter	Symbol	Typ	Units
Supply Voltage	V_{CC}	-0.3 to 20	V
Operating Supply Voltage	V_{CC}	-0.3 to 16.5	V
Input Voltages	V_{INA}, V_{INB}	-0.3 to V_{CC}	V
Peak Output Currents	I_{OUTA}, I_{OUTB}	3	A
Enable Voltage	V_{EN}	-0.3 to V_{CC}	V
Shutdown Voltage	V_{SHDN}	-0.3 to V_{CC}	V
Continuous Power Dissipation	P_d	Internally limited	W
Operating Temperature Range	T_A	-40 to +85	°C
Thermal Resistance Junction to Ambient (MSOP)	θ_{JA}	206	°C/W
Thermal Resistance Junction to Ambient (SOIC)	θ_{JA}	165	°C/W
Storage Temperature Range	T_{STG}	-65 to +150	°C
Lead Temperature (Soldering)10 sec	T_{LEAD}	260	°C

DC Electrical Characteristics

Unless otherwise specified: $T_A = 25^\circ\text{C}$, $V_{CC} = 12\text{V}$, $V_{IN} = 5\text{V}$, $V_{EN} = 5\text{V}$, $V_{SHDN} = 5\text{V}$

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Supply Current						
Quiescent Current	I_Q	$V_{CC} < V_{START}$			1.5	mA
Quiescent Current	I_Q	$V_{EN} = V_{SHDN} = V_{INA} = V_{INB} = 3\text{V}$			7.5	mA
Quiescent Current	I_Q	$V_{SHDN} = 0\text{V}$			6	μA
Under-Voltage Lockout						
Threshold Voltage	V_{START}	$V_{SHDN} = V_{EN} = V_{INA} = V_{INB} = 3\text{V}$		4.5		V
Hysteresis		$V_{SHDN} = V_{EN} = V_{INA} = V_{INB} = 3\text{V}$		320		mV
Enable						
Enable Voltage	V_{EN}	$0 < V_{EN} < V_{CC}$	2.0			V
Disable Voltage	V_{EN}	$0 < V_{EN} < V_{CC}$			0.8	V
Delay to Output	t_{D_EN}	EN from low to high		70		ns
Delay to Output	t_{D_DIS}	EN from high to low		55		ns
Enable Input Current	I_{EN}	$0 < V_{EN} < V_{CC}$		14		μA
Input						
High Level Input Voltage	V_{IH}	$0 < V_{IN} < V_{CC}$	2.0			V
Low Level Input Voltage	V_{IL}	$0 < V_{IN} < V_{CC}$			0.8	V
Input Current	I_{IN}	$0 < V_{IN} < V_{CC}$ Non-Inverting Input(s) of SC1302A/C			16	μA
		$0 < V_{IN} < V_{CC}$ Inverting Input(s) of SC1302B/C	-7			μA

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DC Electrical Characteristics (Cont.)

Unless otherwise specified: $T_A = 25^{\circ}\text{C}$, $V_{CC} = 12\text{V}$, $V_{IN} = 5\text{V}$, $V_{EN} = 5\text{V}$

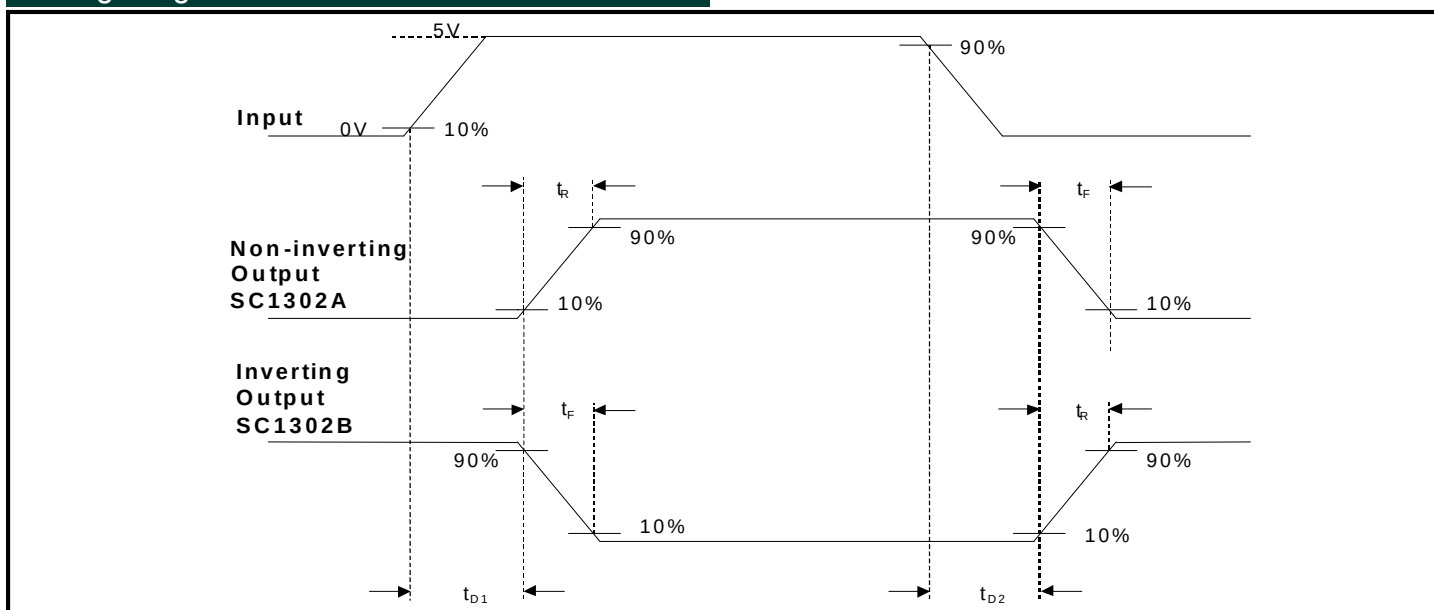
Parameter	Symbol	Conditions	Min	Typ	Max	Units
Output						
Output Peak Current	I_{PK_SOURCE}	$V_{OUT} = 0.5\text{V}$, $t_{PW} < 10\mu\text{s}$		1600		mA
	I_{PK_SINK}	$V_{OUT} = V_{CC} - 0.5\text{V}$, $t_{PW} < 10\mu\text{s}$		1600		mA
Shutdown						
$\overline{\text{SHDN}}$ Input Voltage High	$V_{\overline{\text{SHDN}}}$		2			V
$\overline{\text{SHDN}}$ Input Voltage Low	$V_{\overline{\text{SHDN}}}$				0.3	V
$\overline{\text{SHDN}}$ Pin Current	$I_{\overline{\text{SHDN}}}$	$V_{\overline{\text{SHDN}}} = 5\text{V}$		30		μA
Thermal Shutdown						
Over Temperature Trip Point	T_{J_OT}			150		$^{\circ}\text{C}$
Hysteresis				10		$^{\circ}\text{C}$

AC Electrical Characteristics

Unless otherwise specified: $T_A = 25^{\circ}\text{C}$, $V_{CC} = 12\text{V}$, $V_{EN} = 5\text{V}$, $C_L = 1000\text{pF}$

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Rise time	t_R	See Timing Diagram		20		ns
Fall time	t_F	See Timing Diagram		20		ns
Propagation delay time	t_{D1}	See Timing Diagram		53		ns
Propagation delay time	t_{D2}	See Timing Diagram		41		ns

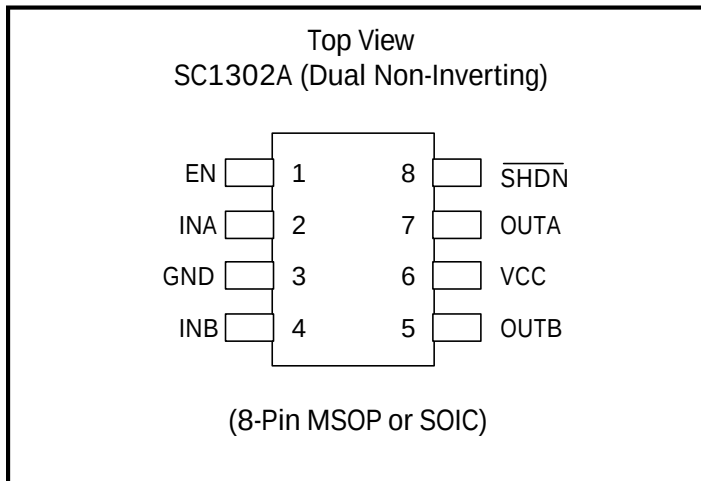
Timing Diagrams



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Pin Configuration

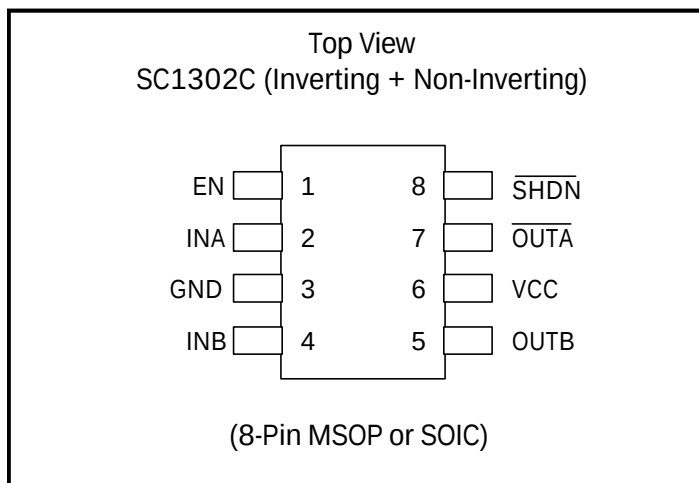
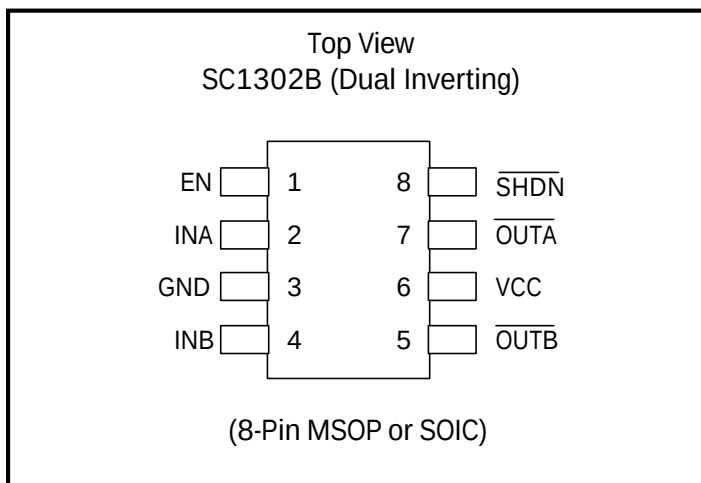


Ordering Information

Part Number	Package	Temp. Range (T _A)
SC1302AIMSTR	MSOP-8	-40°C to +85°C
SC1302BIMSTR		
SC1302CIMSTR		
SC1302AISTR	SOIC-8	-40°C to +85°C
SC1302BISTR		
SC1302CISTR		

Note:

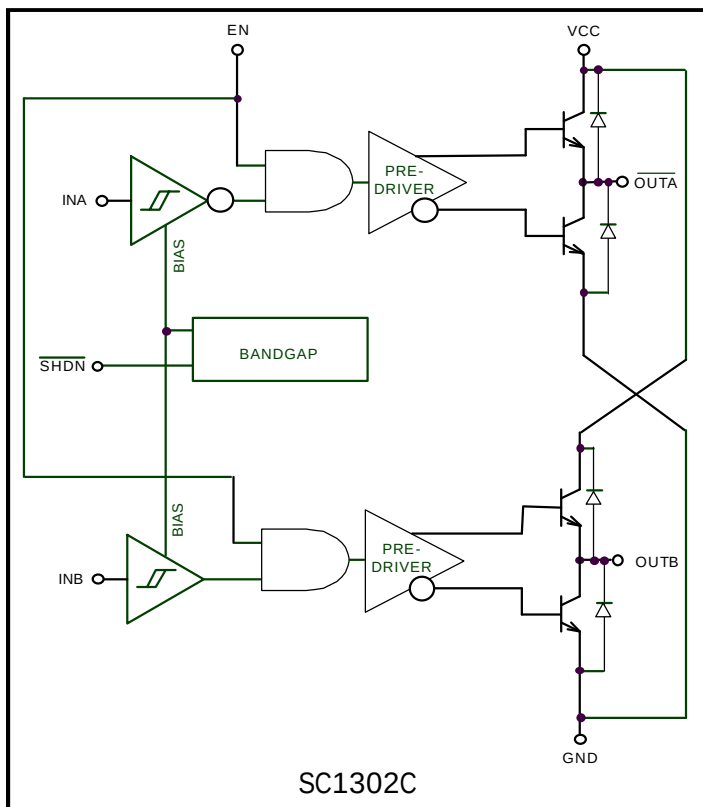
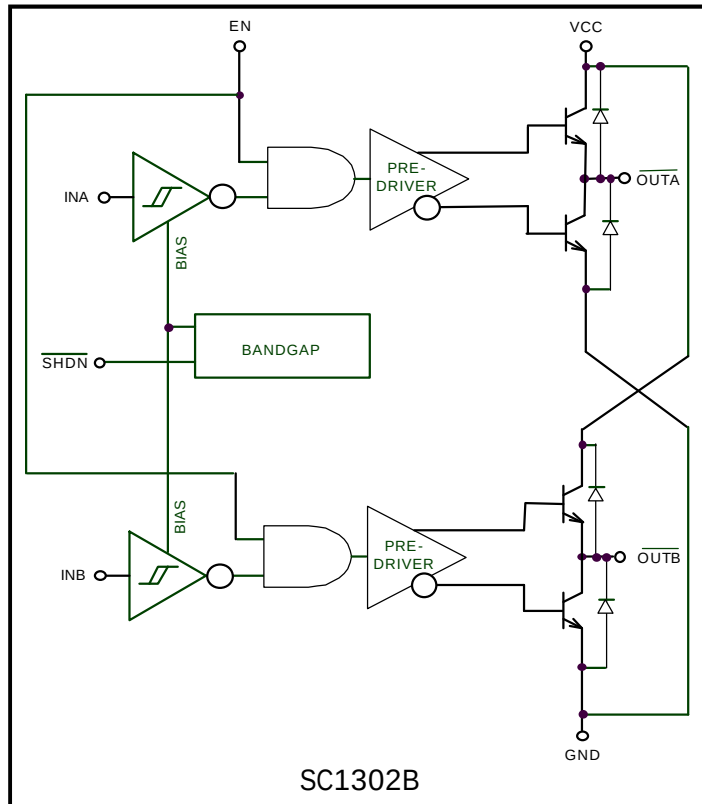
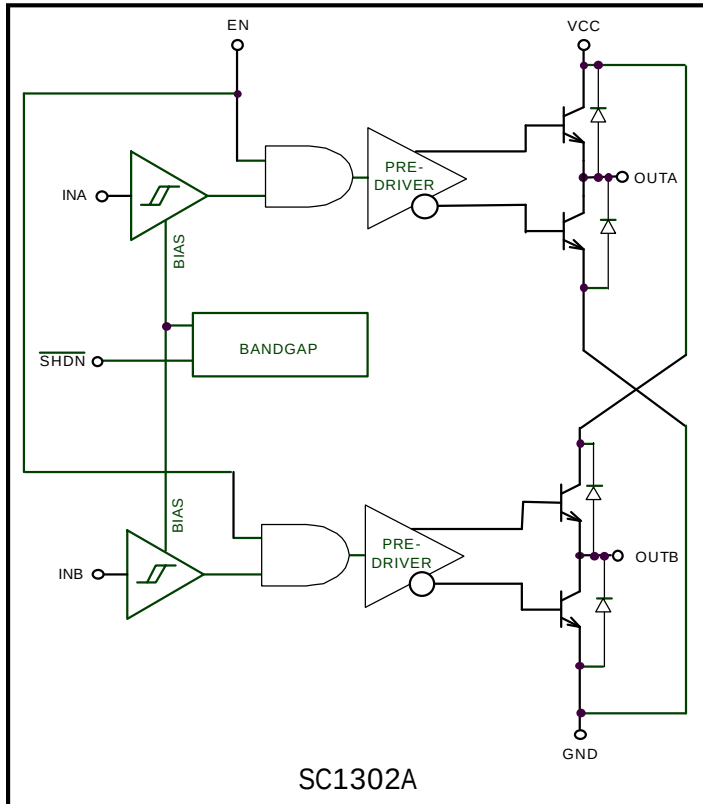
(1) Only available in tape and reel packaging. A reel contains 2500 devices.



Pin Descriptions

Pin #	SC1302A	SC1302B	SC1302C	Pin Function
1	EN	EN	EN	Enable/disable control. When the EN is driven low, both outputs are low. When left open, both outputs are low. Enable both drivers by tying EN pin to a voltage greater than 2V.
2	INA	INA	INA	TTL-compatible input to the driver A. When left open, Pin 7 is low.
3	GND	GND	GND	Ground.
4	INB	INB	INB	TTL-compatible input to the driver B. When left open, Pin 5 is low.
5	OUTB	$\overline{\text{OUTB}}$	OUTB	Output gate drive B for external MOSFET.
6	VCC	VCC	VCC	Supply: +4.5V to +16.5V supply. During UMLO, the outputs are held low.
7	OUTA	$\overline{\text{OUTA}}$	$\overline{\text{OUTA}}$	Output gate drive A for external MOSFET.
8	$\overline{\text{SHDN}}$	$\overline{\text{SHDN}}$	$\overline{\text{SHDN}}$	Shutdown pin. Apply a voltage from 2V to VCC to enable device. Pull below 0.3V for low-power shut down.

Block Diagrams



Applications Information

The SC1302A/B/C is a high speed, high peak current dual MOSFET driver. It is designed to drive power MOSFETs with ultra-low rise/fall time and propagation delays. As the switching frequency of PWM controllers is increased to reduce power converters volume and cost, fast rise and fall times are necessary to minimize switching losses. While discrete solution can achieve reasonable drive capability, implementing delay and other housekeeping functions necessary for safe operation can become cumbersome and costly. The SC1302A/B/C presents a total solution for the high-speed, high power density applications. Wide input supply range of 4.5V - 16.5V allows use in battery powered applications as well as distributed power systems.

Supply Bypass and Layout

A 4.7μF to 10μF tantalum bypass capacitor with low ESR (equivalent series resistance) and an additional 0.1μF ceramic capacitor in parallel are recommended as supply bypass to control switching and supply transients.

As with any high speed, high current circuit, proper layout is critical in achieving optimum performance of the SC1302A/B/C. Attention should be paid to the proper placement of the driver, the switching MOSFET and the bypass capacitors.

The driver should be placed as close as possible to the external MOSFET's to eliminate the possibility of oscillation caused by trace inductance and the MOSFET gate capacitance. A resistor in the range of 10Ω could be used in series with the gate drive to damp the ringing if the drive output path is not short enough. The bypass capacitors should also be placed closely between Vcc and GND of the driver.

Drive Capability and Power Dissipation

The SC1302A/B/C is able to deliver 1.6A peak current for driving capacitive loads, such as MOSFET's.

Fast switching of the MOSFET's significantly reduces switching losses for high frequency applications. Thermal stress is reduced and system reliability is improved.

For simplicity, we assume that the gate capacitance of a MOSFET is constant. The power delivered from the power supply can be estimated based on this simplification. The energy needed to charge the capacitor is given by:

$$E_{ON} = \frac{1}{2} \cdot C \cdot V^2$$

where C is the load capacitance and V is the output voltage swing of the driver.

During turn off, the same amount of energy is dumped to the ground. Therefore, the energy dissipated in one switching cycle is:

$$E_{TOTAL} = C \cdot V^2$$

The power dissipation due to the gate driving actions is given by:

$$P_{GATE} = f \cdot C \cdot V^2$$

where, f is the switching frequency.

with $V_{CC}=12V$, $C=1nF$ and $f=200kHz$, the power dissipation per output is:

$$P_{GATE} = (200kHz) \cdot (1nF) \cdot (12)^2 = 29mW$$

The corresponding supply current is:

$$I = \frac{P_{GATE}}{V_{CC}} = \frac{29mW}{12V} = 2.4mA$$

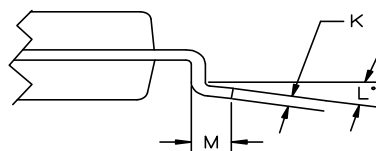
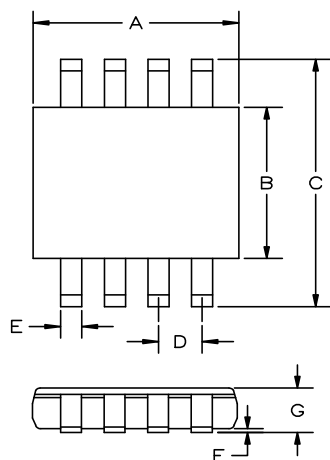
Thermal Information

The driver's junction temperature must be kept within the rated limit at any time. The application system has to effectively remove the heat generated in the driver in order for proper functions and performance. If the junction temperature reaches 150°C, the internal protection circuit will be triggered to shut down the gate driver.

The power dissipation of the SC1302A/B/C should be derated according to the following formula:

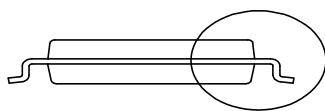
$$\text{Power Dissipation} < \frac{125^{\circ}C - T_A}{\theta_{JA}}$$

where T_A = ambient temperature.

Outline Drawing - MSOP-8


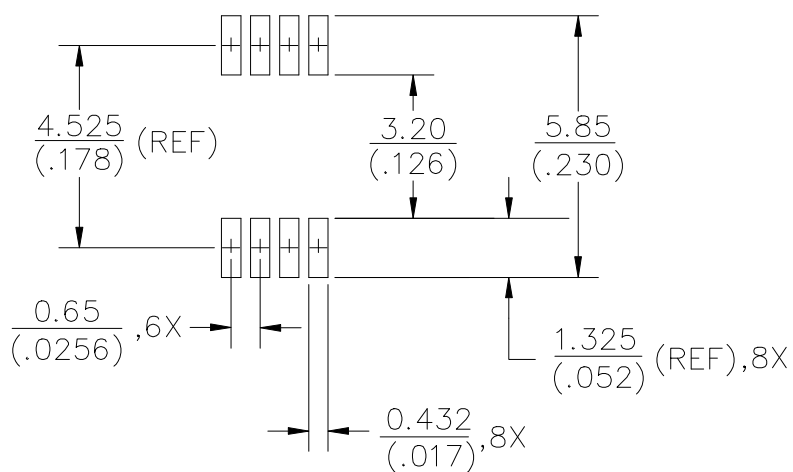
DETAIL "A"

DIM ^N	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.114	.122	2.90	3.10	
B	.114	.122	2.90	3.10	
C	.187	.199	4.75	5.05	
D	.025	BSC	.65	BSC	
E	.010	.016	.25	.40	
F	.002	.006	.05	.15	
G	—	.043	—	1.10	
K	.005	.009	.13	.23	
L	0°	6°	0°	6°	
M	.016	.028	.40	.70	



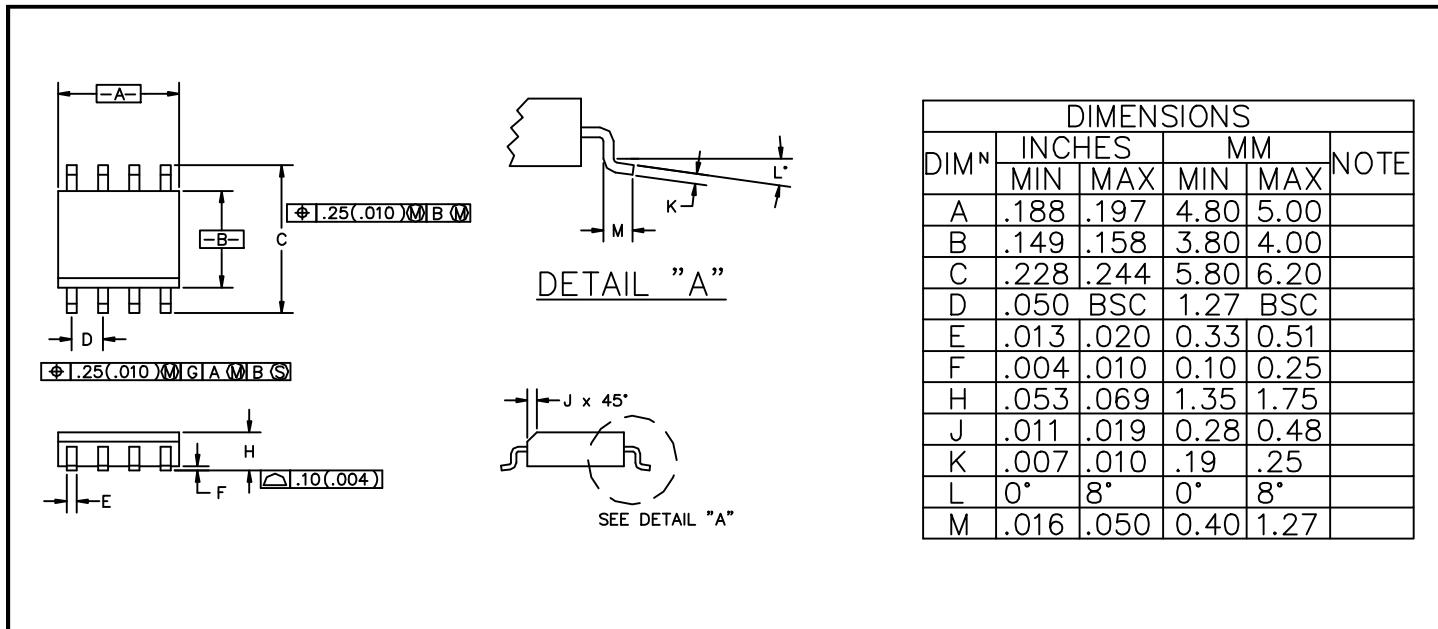
SEE DETAIL "A"

- ② PACKAGE OUTLINE EXCLUSIVE OF MOLD FLASH AND METAL BURR.
 ① CONTROLLING DIMENSIONS: MILLIMETERS.

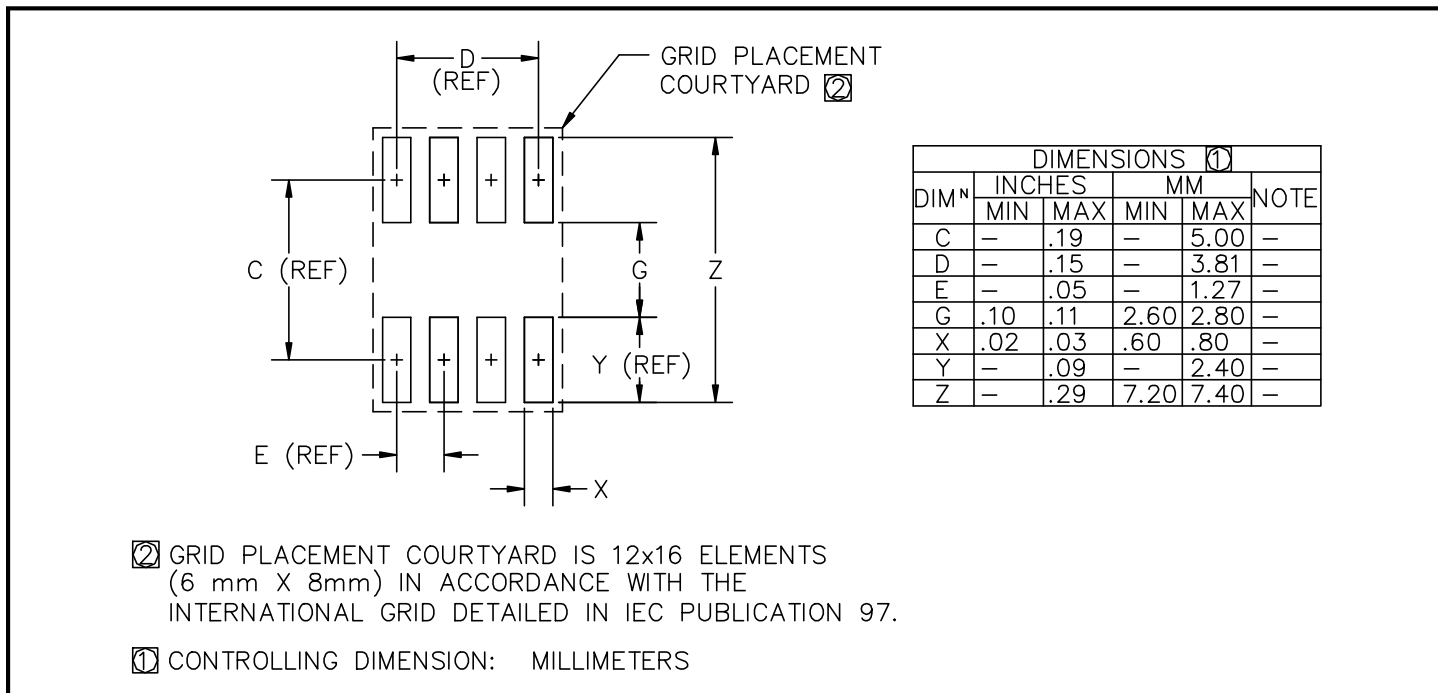
Land Pattern - MSOP-8


- ① DIMENSIONS ARE IN MILLIMETERS (INCHES).

Outline Drawing - SO-8



Land Pattern - SO-8



Contact Information

Semtech Corporation
Power Management Products Division
200 Flynn Rd., Camarillo, CA 93012
Phone: (805)498-2111 FAX (805)498-3804